

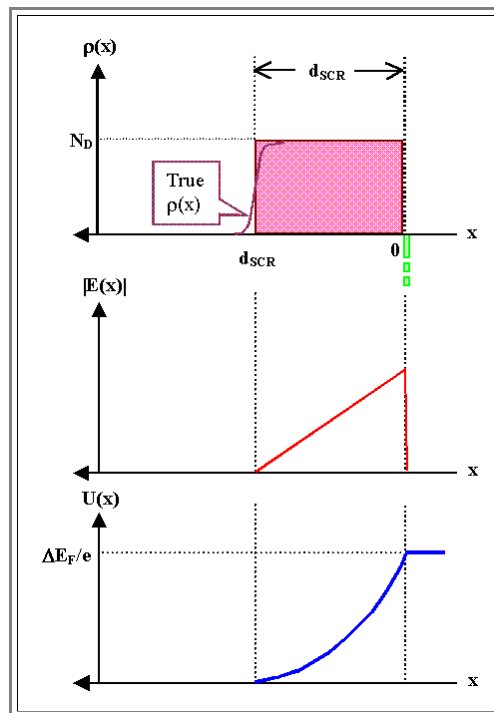
Space Charge Region and Poisson Equation

Illustration

- We start from a (constant) distribution of positive charges (for n-doped semiconductors) in the space charge region.
- The corresponding negative charges are all on the surface; the charge distribution is shown in the first frame of the illustration.
- [Poisson's equation](#) states that (for the one-dimensional case).

$$\epsilon \epsilon_0 \frac{d^2 V(x)}{dx^2} = - \rho(x) = e \cdot N_D$$

- For $0 < x < d_{SCR}$ and $= 0$ everywhere else. (We can also use the voltage $U(x)$ instead of $V(x)$ if we think as $V(x = \infty) = 0$). That will also be reflected in the choice of boundary conditions made below.
- The drawing below shows the situation, including the slight approximation implicit in our choice of $\rho(x)$. Note that the x -direction is to the left in this case.



- The first straight-forward integration yields $dU/d(x)$ which is the electrical field strength $E_x = -dU/dx$, or

$$\epsilon \epsilon_0 \frac{dV(x)}{dx} = - \epsilon \epsilon_0 E_x = e \cdot N_D \cdot x + \text{const.}$$

- With the boundary condition $E_x(x = d_{SCR}) = 0$, we obtain (always for the interval $x = 0$ and $x = d_{SCR}$, of course):

$$e \cdot N_D \cdot d_{SCR} + \text{const} = 0$$

$$\text{const} = - e \cdot N_D \cdot d_{SCR}$$

$$E_x = \frac{1}{\epsilon \epsilon_0} \cdot (e \cdot N_D d_{SCR} - e \cdot N_D \cdot x)$$

- The second integration yields

$$\epsilon \epsilon_0 \cdot U(x) = \frac{e \cdot N_D \cdot x^2}{2} - e \cdot N_D \cdot d_{SCR} \cdot x + \text{const.}$$

- With the boundary condition $U(d_{SCR}) = 0$, we obtain .

$$-\frac{e \cdot N_D \cdot d_{SCR}^2}{2} + \text{const.} = 0$$

$$\text{const.} = \frac{e \cdot N_D \cdot d_{SCR}^2}{2}$$

- Using the proper expression for the integration constant gives us the complete voltage function or the shape of the band bending

$$\epsilon \epsilon_0 \cdot U(x) = \frac{e \cdot N_D \cdot x^2}{2} - e \cdot N_D \cdot d_{SCR} \cdot x + \frac{e \cdot N_D \cdot d_{SCR}^2}{2}$$

- The width of the space charge region can be obtained by considering the voltage at $x = 0$, where we have $U(x = 0) = \Delta E_F / e$. Using this we obtain

$$\frac{\epsilon \epsilon_0}{e} \cdot \Delta E_F = \frac{e \cdot N_D \cdot d_{SCR}^2}{2}$$

- This gives us the final result for the width of the space charge region

$$d_{SCR} = \frac{1}{e} \cdot \left(\frac{2 \Delta E_F \cdot \epsilon \epsilon_0}{N_D} \right)^{1/2}$$

- The corresponding curves are shown in the drawing above. We obtained the [same formula as before](#), but now we have a better awareness of the approximations it contains.
 - The positive charge distribution was assumed to be box-shaped and uniform. This is a rather good approximation; the drawing indicates the precise shape of the charge distribution for comparison.
 - The counter charges are described by a δ -function at the surface; these charges only enter the calculation in the indirect form of a boundary condition.